

ABSTRACT

The present invention provides a chemical metal polishing (CMP) method with improved flexibility and improved processing window, especially as it relates to the chemical aspect of CMP technology. Broadly speaking, the invention has two aspects: according to 5 one aspect, the invention provides a new CMP composition, comprising as an oxidizer, at least one of inorganic halogen derivative and dissolved oxygen while in a second aspect the invention provides an improved method for polishing metals.